

## N-Channel Power MOSFET

### FEATURES

- Low RDS(ON) 250mΩ (Max.)
- Low gate charge typical @ 3.9nC (Typ.)
- RoHS compliant
- Halogen-free

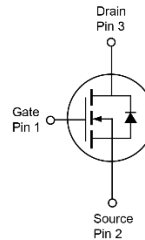
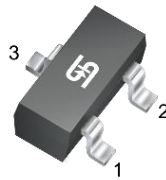
### APPLICATIONS

- DC-DC Converters
- Power management functions

KEY PERFORMANCE PARAMETERS			
PARAMETER		VALUE	UNIT
V <sub>DS</sub>		100	V
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	250	mΩ
Q <sub>g</sub>		3.9	nC



SOT-23



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	1.5	A
Pulsed Drain Current (Note 1)	I <sub>DM</sub>	6	A
Total Power Dissipation	P <sub>D</sub>	T <sub>A</sub> = 25°C	1.04
		T <sub>A</sub> = 70°C	0.67
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Ambient Thermal Resistance (Note 2)	R <sub>θJA</sub>	120	°C/W

**Notes:**

1. Pulse Width ≤ 100μs.
2. Device on a PCB FR4 with 1 in<sup>2</sup> (single layer, 2 oz thickness) copper area for drain connection.

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b> (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$	100	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	1	1.7	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	$I_{DSS}$	--	--	1	$\mu A$
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.5A$	$R_{DS(on)}$	--	120	250	m $\Omega$
Forward Transconductance	$V_{DS} = 10V, I_D = 0.4A$	$g_{fs}$	--	2.4	--	S
<b>Dynamic</b> (Note 4)						
Total Gate Charge	$V_{DS} = 50V, I_D = 1.5A,$ $V_{GS} = 10V$	$Q_g$	--	3.9	--	nC
Gate-Source Charge		$Q_{gs}$	--	0.6	--	
Gate-Drain Charge		$Q_{gd}$	--	1	--	
Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	$C_{iss}$	--	142	--	pF
Output Capacitance		$C_{oss}$	--	32	--	
Reverse Transfer Capacitance		$C_{rss}$	--	13	--	
<b>Switching</b> (Note 5)						
Turn-On Delay Time	$V_{DD} = 50V, R_G = 6\Omega,$ $I_D = 1.5A, V_{GS} = 10V$	$t_{d(on)}$	--	3.2	--	ns
Turn-On Rise Time		$t_r$	--	2.2	--	
Turn-Off Delay Time		$t_{d(off)}$	--	12	--	
Turn-Off Fall Time		$t_f$	--	10	--	
<b>Source-Drain Diode</b>						
Forward Voltage (Note 3)	$I_S = 1.5A, V_{GS} = 0V$	$V_{SD}$	--	0.8	1.2	V

**Notes:**

- Pulse test: Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- Defined by design. Not subject to production test.
- Switching time is essentially independent of operating temperature.

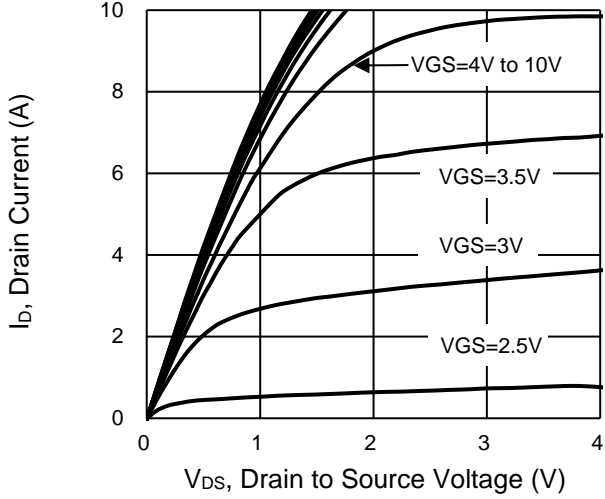
**ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
TSM2328CX RFG	SOT-23	3kpcs / 7" Reel

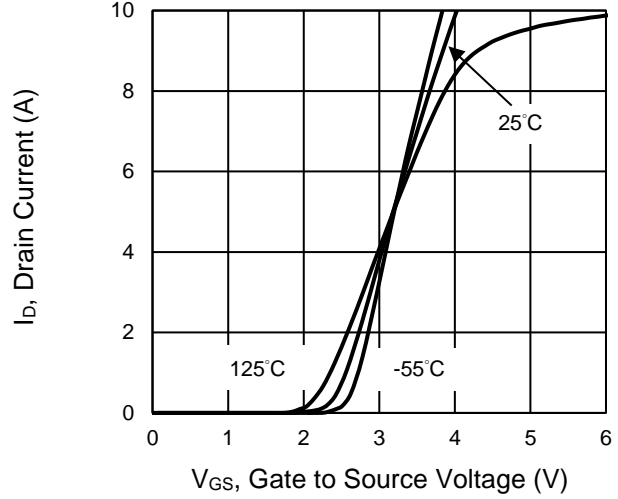
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

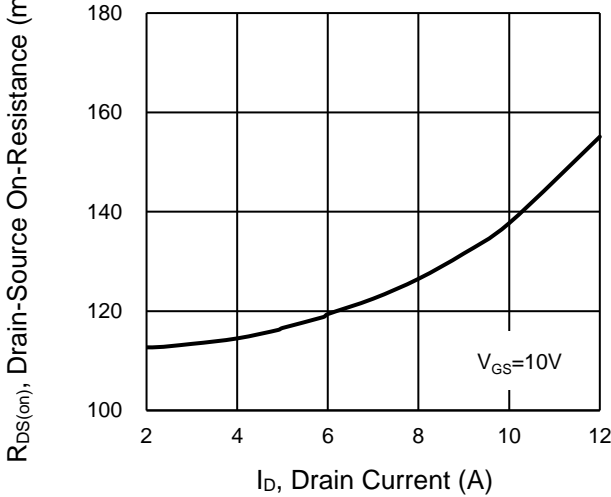
**Output Characteristics**



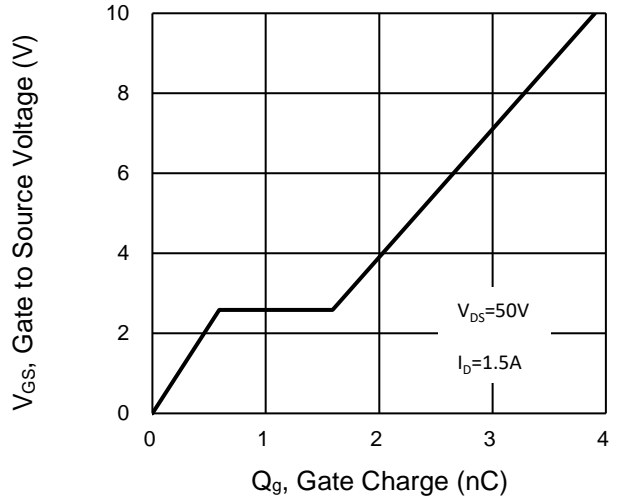
**Transfer Characteristics**



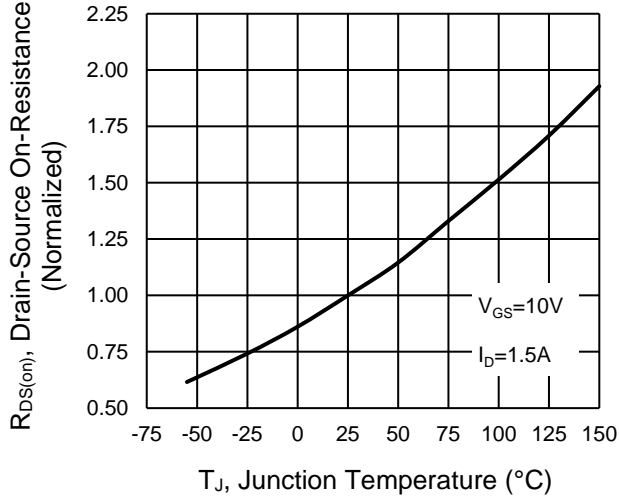
**On-Resistance vs. Drain Current**



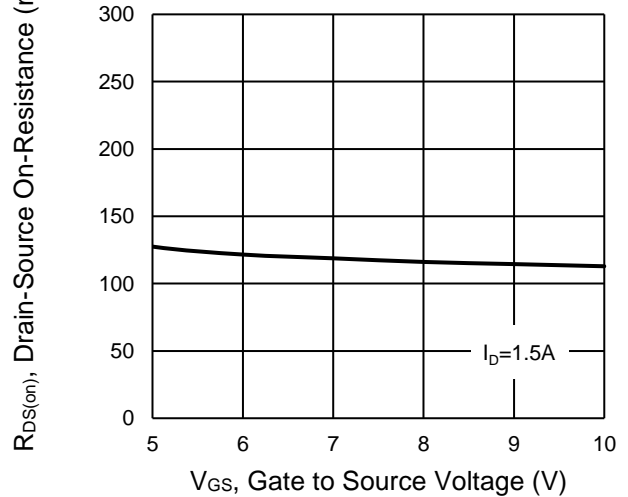
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



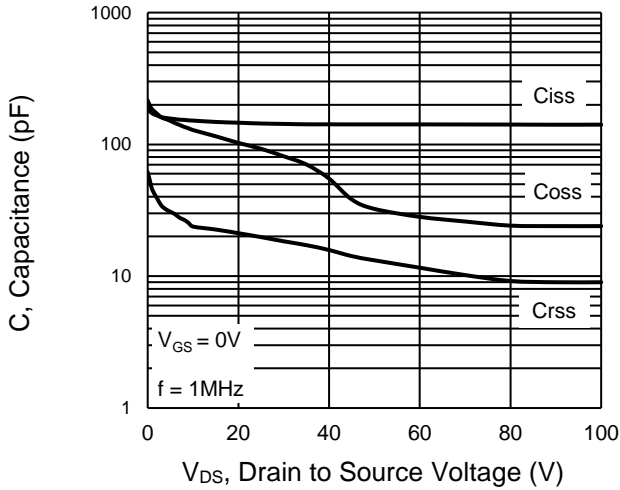
**On-Resistance vs. Gate-Source Voltage**



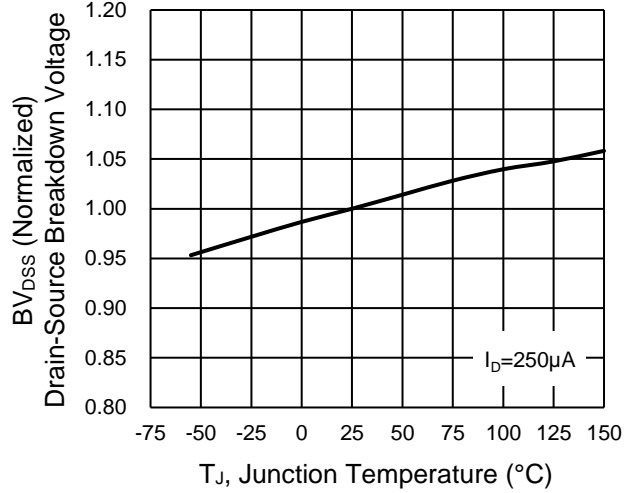
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

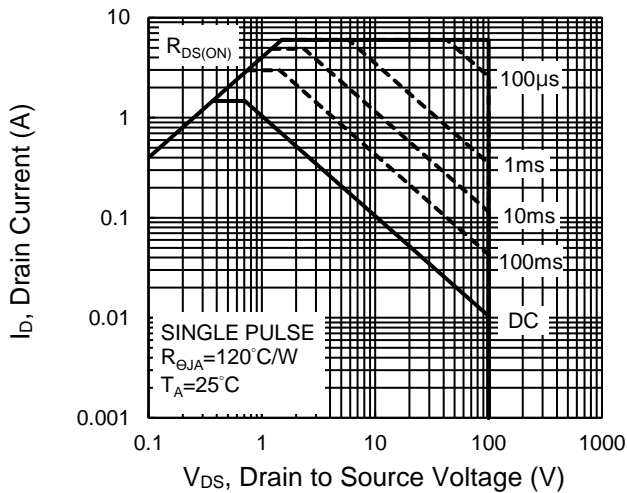
**Capacitance vs. Drain-Source Voltage**



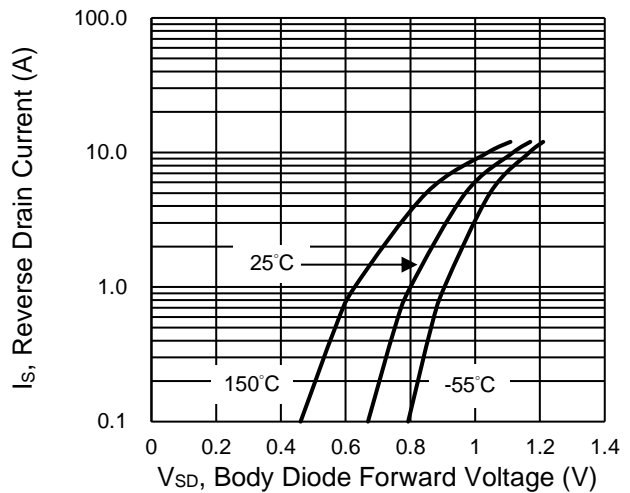
**$BV_{DSS}$  vs. Junction Temperature**



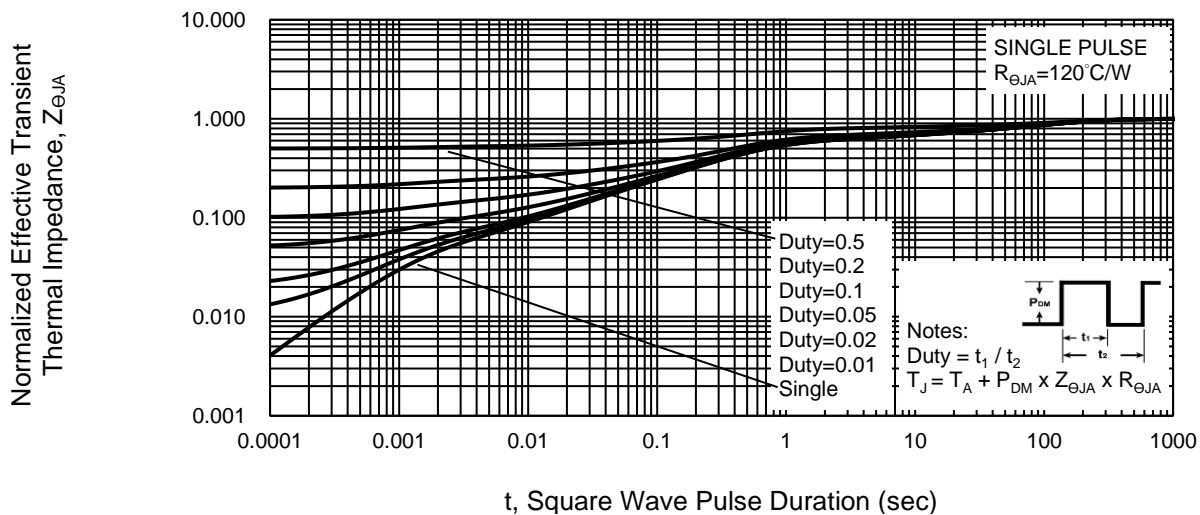
**Maximum Safe Operating Area, Junction-to-Ambient**



**Source-Drain Diode Forward Current vs. Voltage**



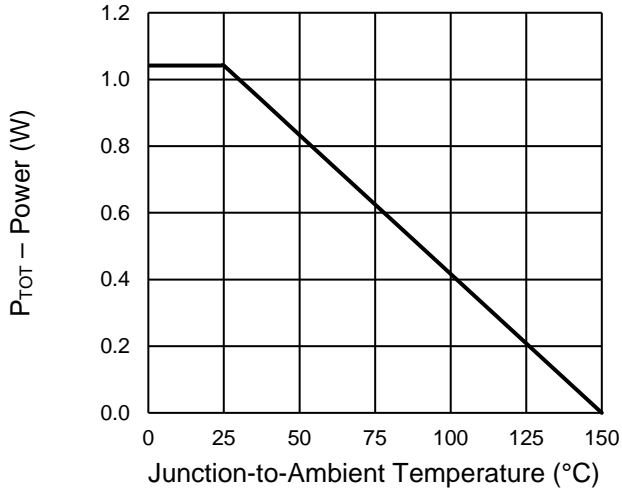
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



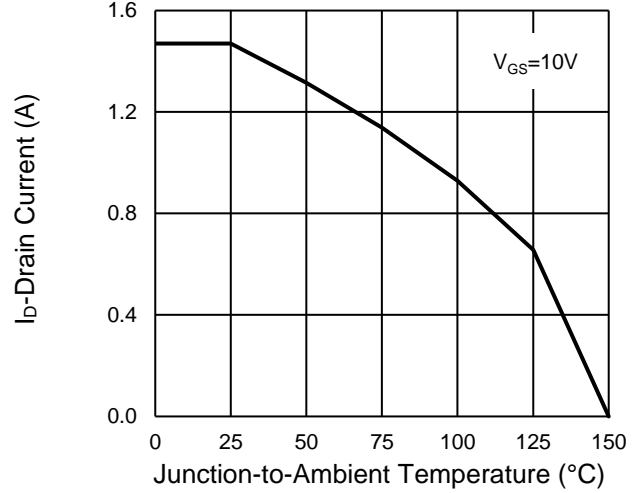
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

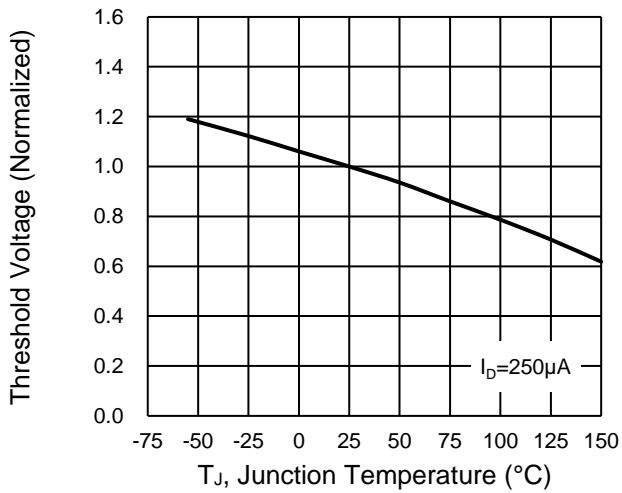
**Power Dissipation**



**Drain Current**

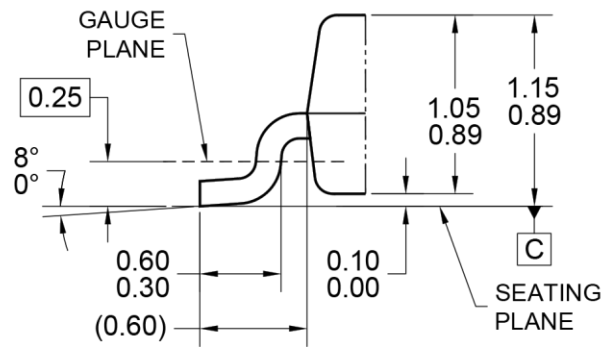
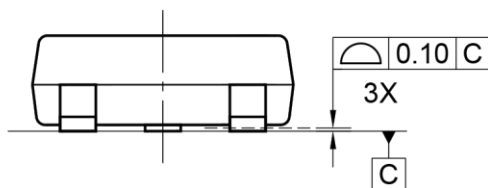
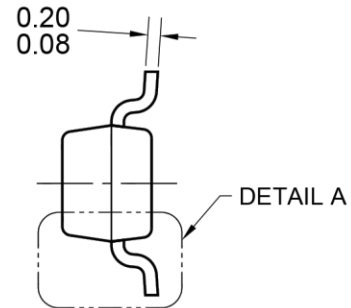
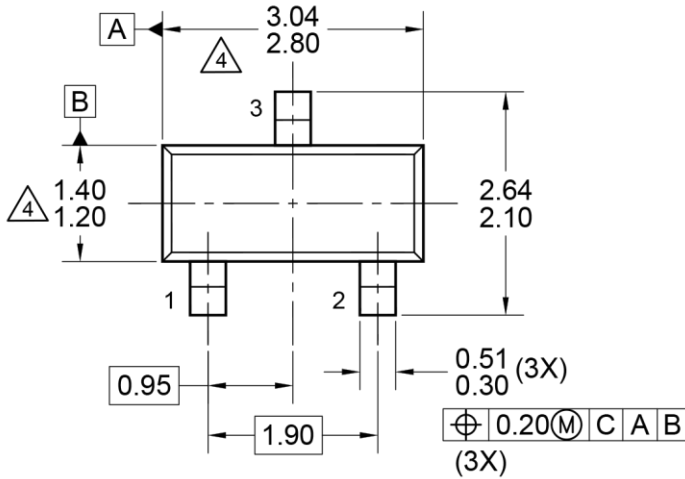


**Normalized gate threshold voltage vs Temperature**

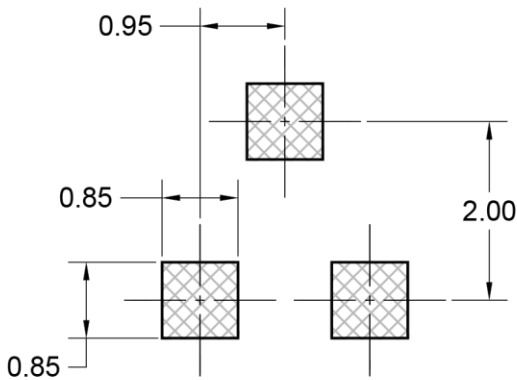


**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

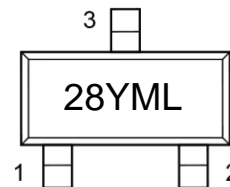
**SOT-23**



DETAIL A, ROTATED -90°  
(SCALE 2:1)



SUGGESTED PAD LAYOUT



**MARKING DIAGRAM**

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEDEC TO-236, ISSUE H, VARIATION AA.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-SOT23JEDEC-104 REV A.

- 28 = Device marking
- Y = Year Code
- M = Month Code for Halogen Free Product  
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code

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